# 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Logic-level compatible
- Very fast switching
- · Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

# 3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	-	60	V	
V <sub>GS</sub>	gate-source voltage			-20	-	20	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	300	mA	
Static characte	Static characteristics (per transistor)							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 5 V; $I_D$ = 50 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.01; $T_j$ = 25 °C		-	1.3	2	Ω	

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



60 V, 300 mA dual N-channel Trench MOSFET

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		
2	G1	gate1		1 + 6
3	D2	drain2	□6 □5 □4	
4	S2	source2		2 5
5	G2	gate2		-   -   ·   ·
6	D1	drain1	TSSOP6 (SOT363)	3 1 1 4
				017aaa055

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
2N7002BKS	TSSOP6	plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

# 7. Marking

Table 4. Marking codes

Type number	Marking code[1]
2N7002BKS	ZT%

[1] % = placeholder for manufacturing site code

### 60 V, 300 mA dual N-channel Trench MOSFET

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	tor			<u> </u>		
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	300	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	215	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.2	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	295	mW
			[1]	-	340	mW
		T <sub>sp</sub> = 25 °C		-	1040	mW
Per device	'			•		-
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	445	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode			1		1
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	300	mA
ESD maxim	num rating			'	'	'
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	2	kV

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

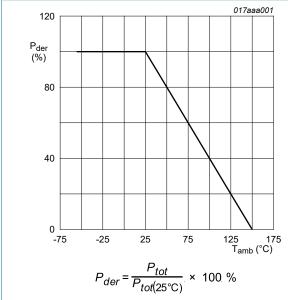


Fig. 1. Normalized total power dissipation as a function of ambient temperature

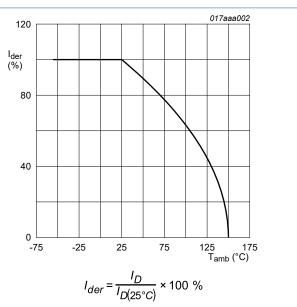


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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### 60 V, 300 mA dual N-channel Trench MOSFET

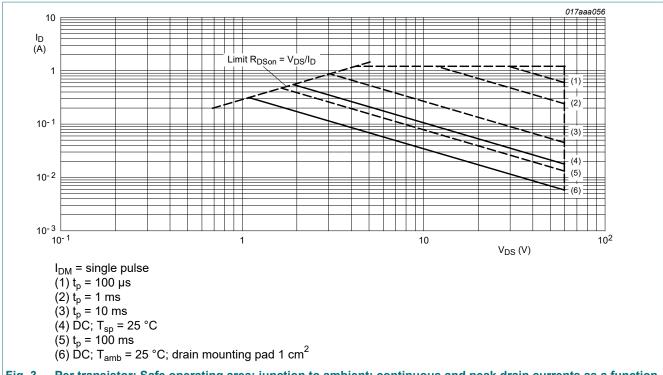


Fig. 3. Per transistor: Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 60 V, 300 mA dual N-channel Trench MOSFET

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	275	K/W
Per transist	tor		,	'			
· -ui(j-a)	thermal resistance from	in free air	[1]	-	370	425	K/W
	junction to ambient		[2]	-	320	370	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	120	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

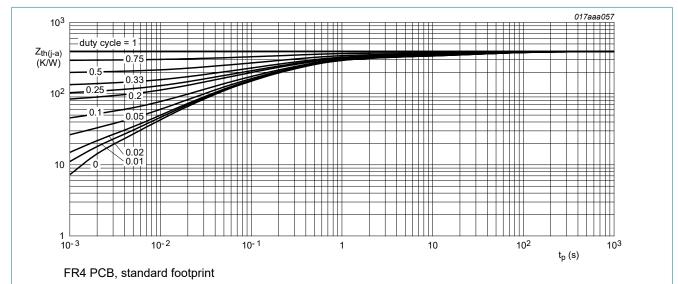


Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

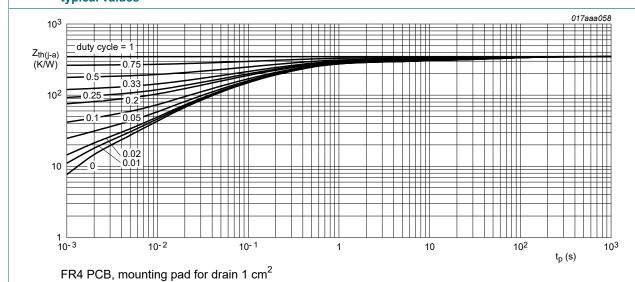


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

2N7002BKS

## 60 V, 300 mA dual N-channel Trench MOSFET

# 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	10	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 5 V; $I_{D}$ = 50 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.01; $T_{j}$ = 25 °C	-	1.3	2	Ω
		$V_{GS}$ = 10 V; $I_D$ = 500 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.01; $T_j$ = 25 °C	-	1	1.6	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 200 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.01; $T_{j}$ = 25 °C	-	550	-	mS
Dynamic ch	aracteristics (per transist	or)				
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 300 mA; V <sub>GS</sub> = 4.5 V;	-	0.5	0.6	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	33	50	рF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	7	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 250 \Omega; V_{GS} = 10 \text{ V};$	-	5	10	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	12	24	ns
t <sub>f</sub>	fall time		-	7	-	ns
Source-drai	in diode (per transistor)					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 115 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	0.47	0.75	1.1	V

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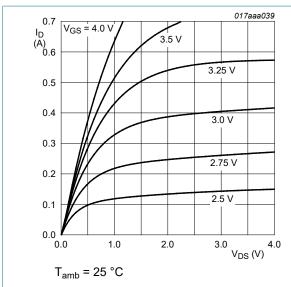
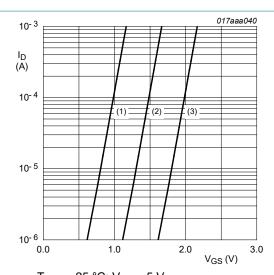


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

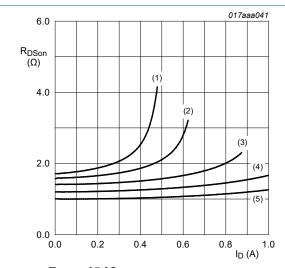


 $T_{amb}$  = 25 °C;  $V_{DS}$  = 5 V (1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



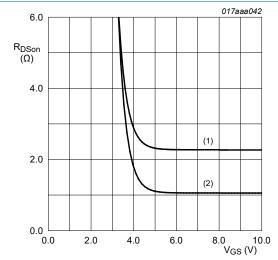
 $T_{amb}$  = 25 °C

(1)  $V_{GS} = 3.25 \text{ V}$  $(2) V_{GS} = 3.5 V$ 

(3)  $V_{GS} = 4 V$ (4)  $V_{GS} = 5 V$ 

 $(5) V_{GS} = 10 V$ 

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 500 \text{ mA}$ 

(1) T<sub>amb</sub> = 150 °C

 $(2) T_{amb} = 25 °C$ 

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

### 60 V, 300 mA dual N-channel Trench MOSFET

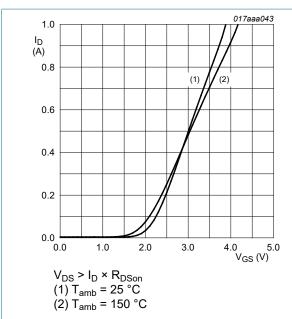


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

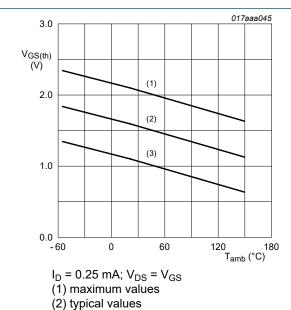


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

(3) minimum values

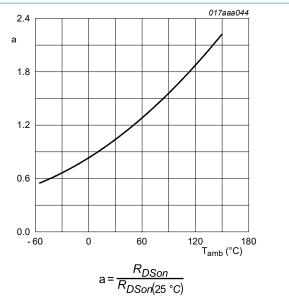
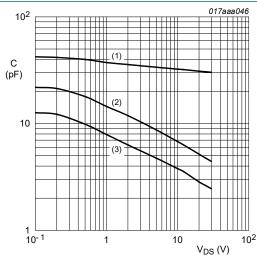


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



- $f = 1 MHz; V_{GS} = 0 V$
- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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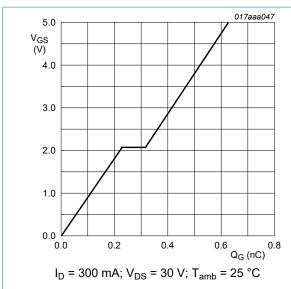


Fig. 14. Gate-source voltage as a function of gate charge; typical values

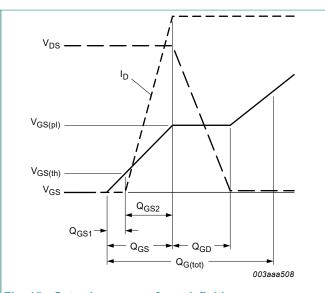
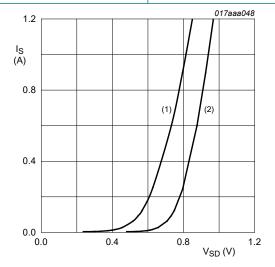


Fig. 15. Gate charge waveform definitions

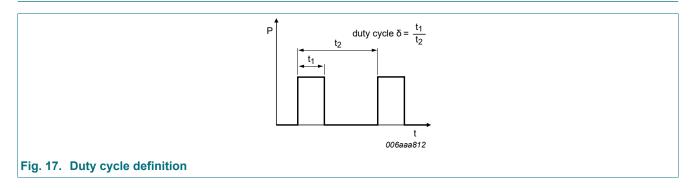


V<sub>GS</sub> = 0 V (1) T<sub>amb</sub> = 150 °C (2) T<sub>amb</sub> = 25 °C

Fig. 16. Source current as a function of source-drain voltage; typical values

60 V, 300 mA dual N-channel Trench MOSFET

## 11. Test information



## **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 60 V, 300 mA dual N-channel Trench MOSFET

# 12. Package outline

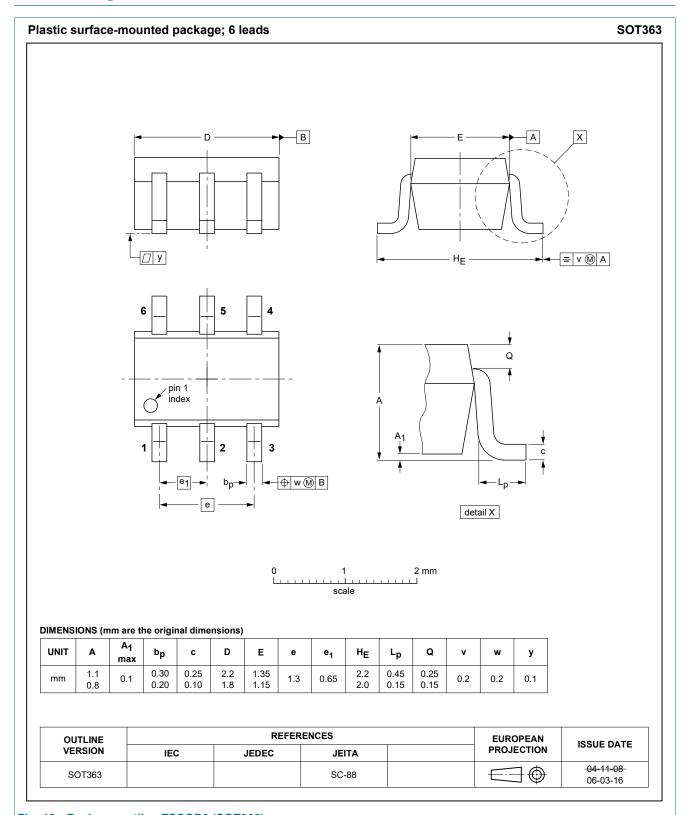
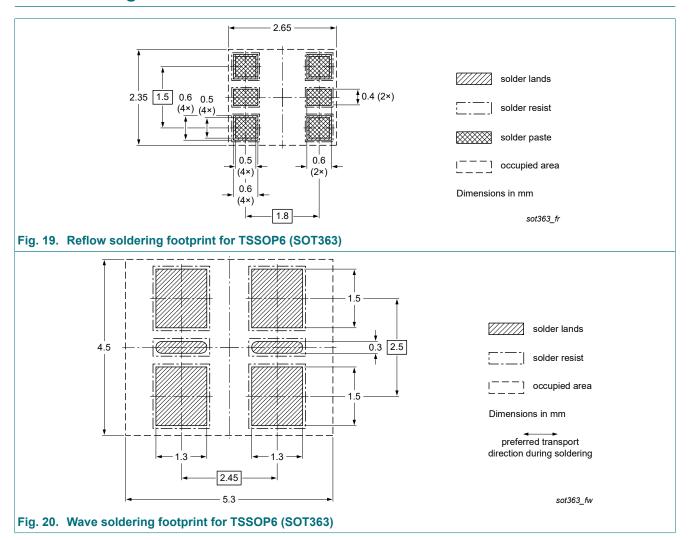


Fig. 18. Package outline TSSOP6 (SOT363)

### 60 V, 300 mA dual N-channel Trench MOSFET

# 13. Soldering



## 60 V, 300 mA dual N-channel Trench MOSFET

# 14. Revision history

### **Table 8. Revision history**

Tubio of Noviolon motory									
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes					
2N7002BKS v.3	20241017	Product data sheet	-	2N7002BKS v.2					
Modifications:	=	<ul> <li>Chapter "Characteristics": Conditions corrected for parameters t<sub>d(on)</sub>, t<sub>r</sub>, t<sub>d(off)</sub>, t<sub>f</sub></li> <li>Chapter "Characteristics": Conditions corrected for Fig. 14</li> </ul>							
2N7002BKS v.2	20100923	Product data sheet	-	2N7002BKS v.1					
2N7002BKS v.1	20100617	Product data sheet	-	-					

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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2N7002BKS

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